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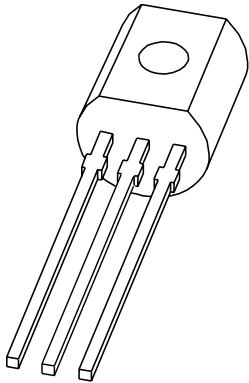
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DATA SHEET



PBSS4350S

50 V low V_{CEsat} NPN transistor

Product data sheet
Supersedes data of 2001 Nov 19

2004 Aug 20

50 V low V_{CEsat} NPN transistor

PBSS4350S

FEATURES

- High power dissipation (830 mW)
- Ultra low collector-emitter saturation voltage
- 3 A continuous current
- High current switching
- Improved device reliability due to reduced heat generation.

APPLICATIONS

- Medium power switching and muting
- Linear regulators
- DC/DC convertor
- Supply line switching circuits
- Battery management applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT54 plastic package.
PNP complement: PBSS5350S.

MARKING

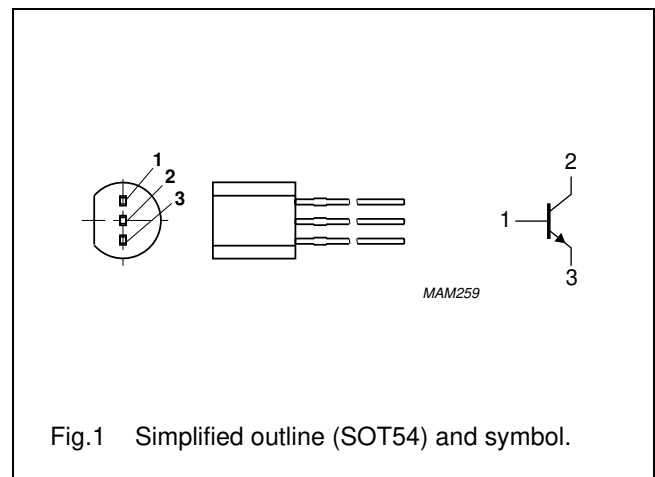
| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PBSS4350S | S4350S |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|-------------|---------------------------|------|------|
| V_{CEO} | collector-emitter voltage | 50 | V |
| I_C | collector current (DC) | 3 | A |
| I_{CM} | peak collector current | 5 | A |
| R_{CEsat} | equivalent on-resistance | <145 | mΩ |

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | collector |
| 3 | emitter |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--------------------------------------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 6 | V |
| I_C | collector current (DC) | | – | 3 | A |
| I_{CM} | peak collector current | | – | 5 | A |
| I_{BM} | peak base current | | – | 1 | A |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ °C}$; note 1 | – | 830 | mW |
| T_{stg} | storage temperature | | –65 | +150 | °C |
| T_j | junction temperature | | – | 150 | °C |
| T_{amb} | operating ambient temperature | | –65 | +150 | °C |

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|---------------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | in free air; note 1 | 150 | K/W |

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

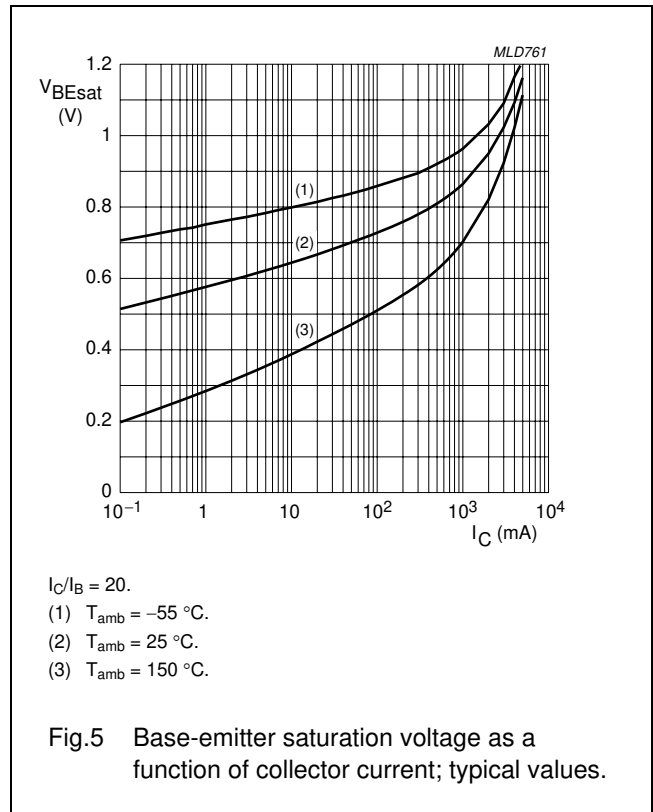
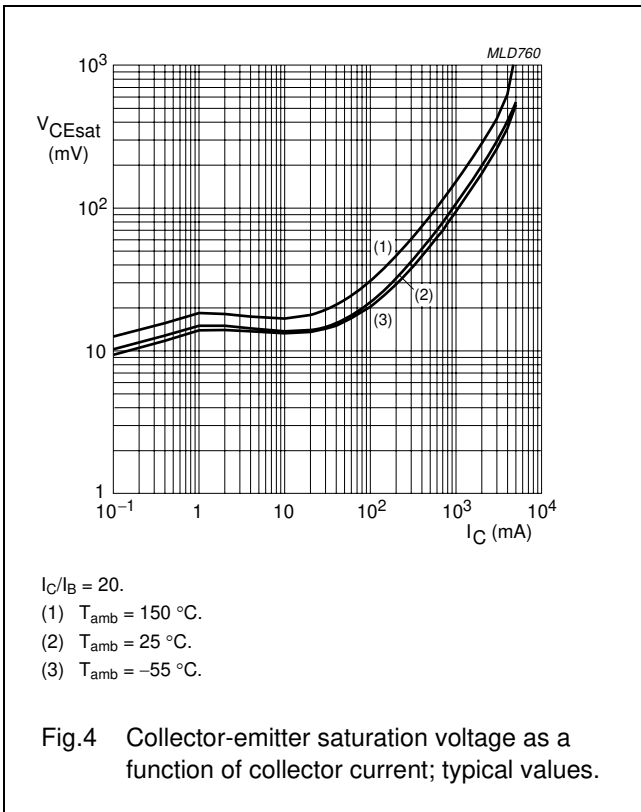
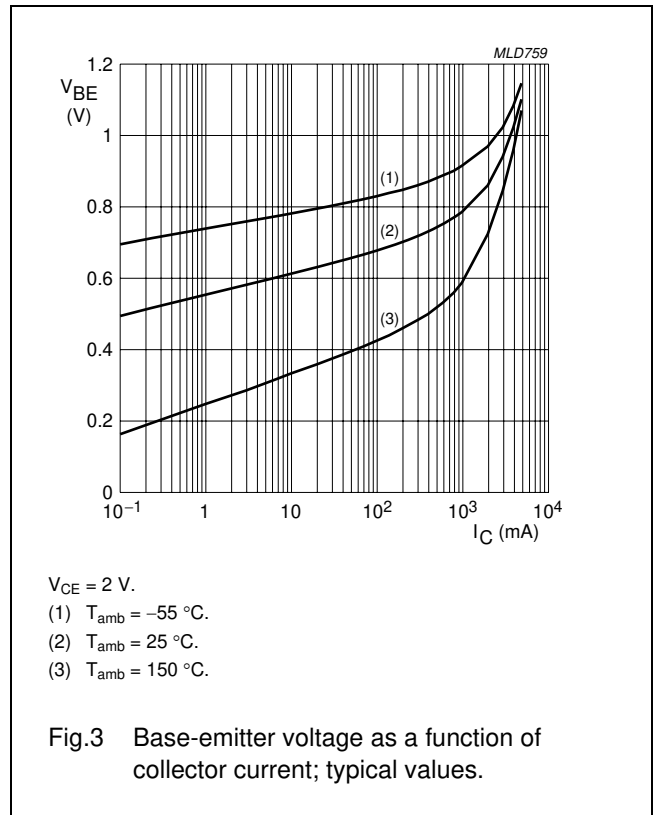
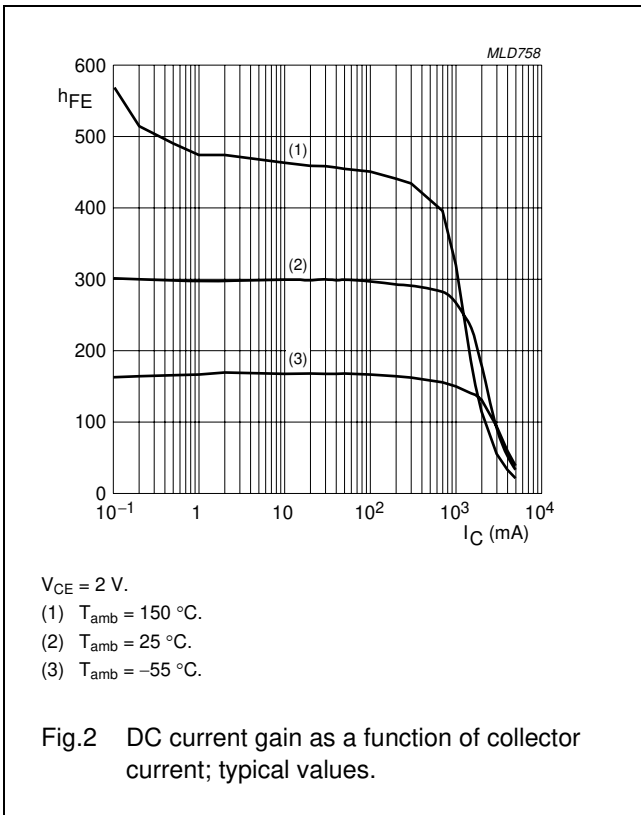
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------|--------------------------------------|--|------|------|------|------------------|
| I_{CBO} | collector-base cut-off current | $V_{CB} = 50\text{ V}; I_E = 0$ | – | – | 100 | nA |
| | | $V_{CB} = 50\text{ V}; I_E = 0; T_j = 150\text{ °C}$ | – | – | 50 | μA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 5\text{ V}; I_C = 0$ | – | – | 100 | nA |
| h_{FE} | DC current gain | $V_{CE} = 2\text{ V}; I_C = 500\text{ mA}$ | 200 | – | – | |
| | | $V_{CE} = 2\text{ V}; I_C = 1\text{ A}; \text{note 1}$ | 200 | – | – | |
| | | $V_{CE} = 2\text{ V}; I_C = 2\text{ A}; \text{note 1}$ | 100 | – | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 500\text{ mA}; I_B = 50\text{ mA}$ | – | – | 90 | mV |
| | | $I_C = 1\text{ A}; I_B = 50\text{ mA}$ | – | – | 170 | mV |
| | | $I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$ | – | – | 290 | mV |
| R_{CEsat} | equivalent on-resistance | $I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$ | – | 110 | <145 | $\text{m}\Omega$ |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$ | – | – | 1.2 | V |
| V_{BEon} | base-emitter turn-on voltage | $V_{CE} = 2\text{ V}; I_C = 1\text{ A}; \text{note 1}$ | – | – | 1.1 | V |
| f_T | transition frequency | $I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$ | 100 | – | – | MHz |
| C_c | collector capacitance | $V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$ | – | – | 30 | pF |

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

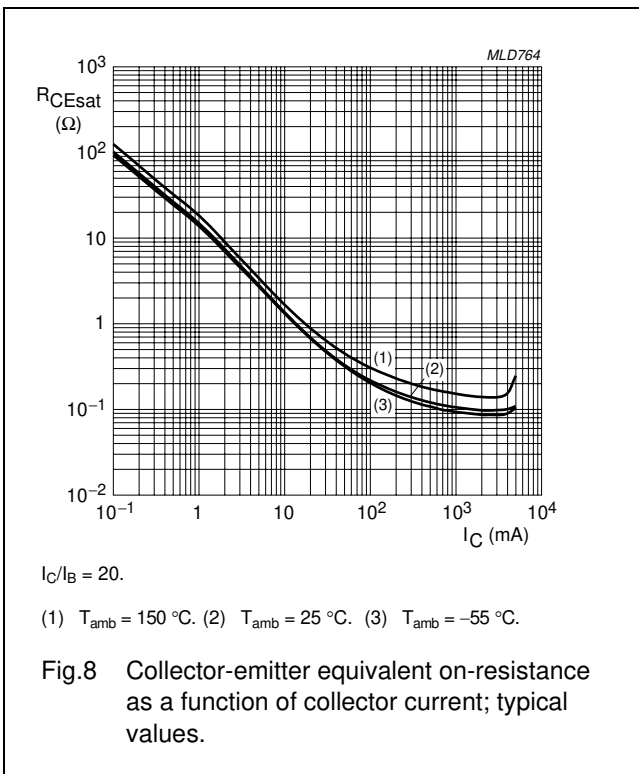
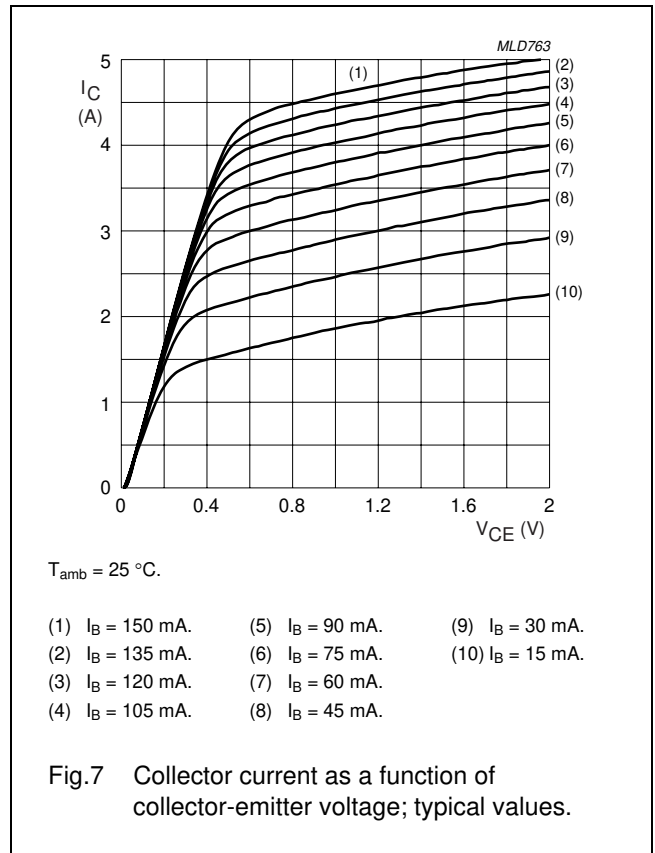
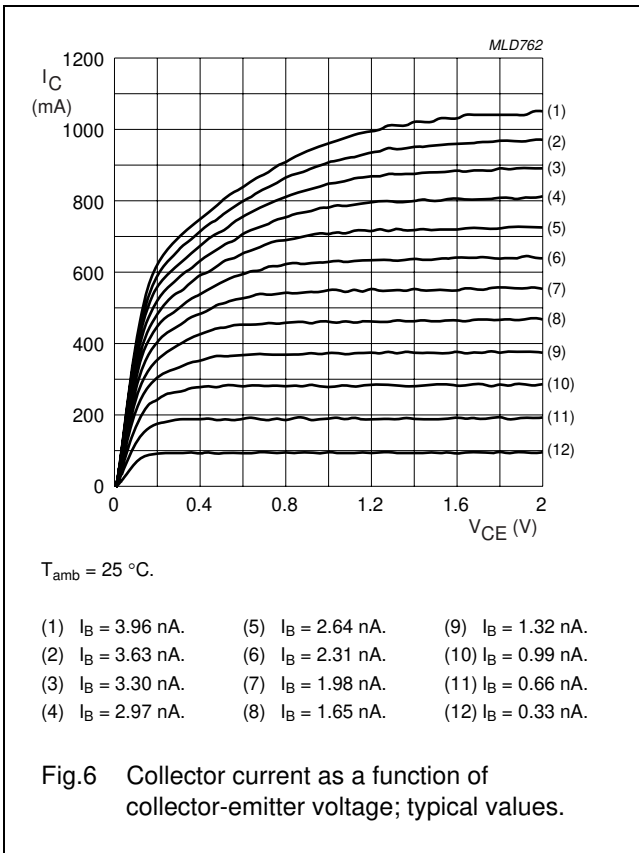
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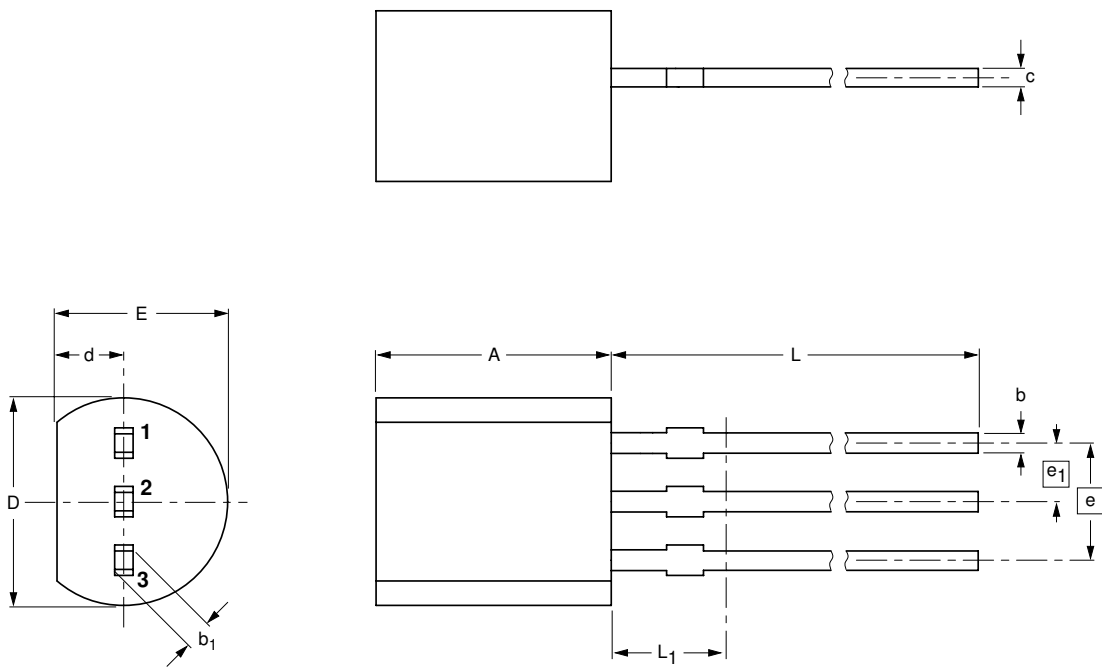
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b | b ₁ | c | D | d | E | e | e ₁ | L | L ₁ ⁽¹⁾ max. |
|------|------------|--------------|----------------|--------------|------------|------------|------------|------|----------------|--------------|---------------------------------------|
| mm | 5.2 5.0 | 0.48 0.40 | 0.66 0.55 | 0.45 0.38 | 4.8 4.4 | 1.7 1.4 | 4.2 3.6 | 2.54 | 1.27 | 14.5 12.7 | 2.5 |

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|--------|------------------------|----------------------|
| | IEC | JEDEC | JEITA | | |
| SOT54 | | TO-92 | SC-43A | | 04-06-28 04-11-16 |

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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